**Product data sheet** 

## 1. Product profile

### 1.1 General description

The KMZ43T is a sensitive magnetic field sensor, employing the magnetoresistive effect of thin-film permalloy. The sensor contains two galvanic separated Wheatstone bridges, at a relative angle of 45° to one another.

A rotating magnetic field in the x-y plane will produce two independent sinusoidal output signals, one a function of  $+\cos(2\alpha)$  and the second a function of  $+\sin(2\alpha)$ ,  $\alpha$  being the angle between sensor and field direction (see <u>Figure 2</u>). The KMZ43T is suited to high precision angle measurement applications under low field conditions (saturation field strength 25 kA/m).

The sensor can be operated at any frequency between 0 Hz and 1 MHz.

#### 1.2 Features

- Accurate and reliable angle measurement
- Mechanical robustness, contactless principle
- Wear-free operation
- Accuracy independent of mechanical tolerances
- Extended temperature range

#### 1.3 Applications

- Steering angle and torsion
- Headlight adjustment
- Motor positioning

- Window wipers
- Fuel level
- Mirror positioning

#### 1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb}$  = 25 °C and  $H_{ext}$  = 25 kA/m;  $V_{CC}$  = 5 V; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		<u>[1]</u> _	5	9	V
$V_{peak}$	peak output voltage	see Figure 2	<u>[1]</u> 60	67	75	mV
V <sub>offset</sub>	offset voltage	per supply voltage; see <u>Figure 2</u>	<u>[1]</u> –2	-	+2	mV/V
R <sub>bridge</sub>	bridge resistance		[1][2] 2.7	3.2	3.7	kΩ

<sup>[1]</sup> Applicable for bridge 1 and bridge 2.

<sup>[2]</sup> Bridge resistance between pin 4 to pin 8, pin 3 to pin 7, pin 1 to pin 5 and pin 2 to pin 6.



Magnetic field sensor

# 2. Pinning information

Table 2. Pinning

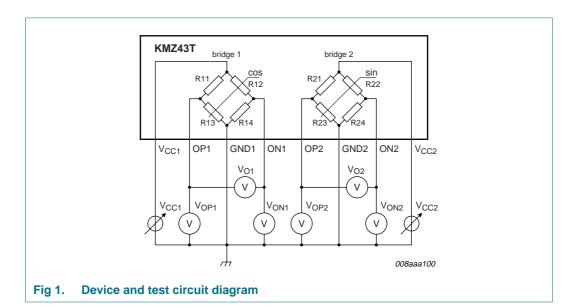
Pin	Symbol	Description	Simplified outline
1	ON1	output voltage bridge 1	
2	ON2	output voltage bridge 2	8
3	$V_{CC2}$	supply voltage bridge 2	
4	V <sub>CC1</sub>	supply voltage bridge 1	
5	OP1	output voltage bridge 1	1 1 1 1 1 1 4
6	OP2	output voltage bridge 2	
7	GND2	ground 2	
8	GND1	ground 1	

# 3. Ordering information

Table 3. Ordering information

Type number	Packag	Package		
	Name	Description	Version	
KMZ43T	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1	

# 4. Circuit diagram



## **Magnetic field sensor**

# 5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage	<u>[1]</u>	-	9	V
H <sub>ext</sub>	external magnetic field strength		25	-	kA/m
T <sub>amb</sub>	ambient temperature		-40	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Applicable for bridge 1 and bridge 2.

## 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		155	K/W

### 7. Characteristics

Table 6. Characteristics

T<sub>amb</sub> = 25 °C and H<sub>ext</sub> = 25 kA/m; V<sub>CC</sub> = 5 V; unless otherwise specified.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CC}$	supply voltage		<u>[1]</u> -	5	9	V
V <sub>peak</sub>	peak output voltage	see Figure 2	<u>[1]</u> 60	67	75	mV
$TC_{Vpeak}$	temperature coefficient of peak output voltage	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +150  ^{\circ}\text{C}$	[1][2] -0.3	-0.36	-0.42	%/K
R <sub>bridge</sub>	bridge resistance		[1][3] 2.7	3.2	3.7	kΩ
TC <sub>Rbridge</sub>	temperature coefficient of bridge resistance	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +150  ^{\circ}\text{C}$	[1][4] 0.24	0.26	0.29	%/K
V <sub>offset</sub>	offset voltage	per supply voltage; see Figure 2	<u>[1]</u> –2	-	+2	mV/V
TC <sub>Voffset</sub>	temperature coefficient of offset voltage	per supply voltage; T <sub>amb</sub> = -40 °C to +150 °C; see <u>Figure 2</u>	<u>[1][5]</u> _4	-	+4	(μV/V)/K
FH	hysteresis of output voltage	see Figure 3	[1][6] 0	0.05	0.18	%FS
k	amplitude synchronism		<u>7</u> 99.5	100	100.5	%
TC <sub>k</sub>	temperature coefficient of amplitude synchronism	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +150  ^{\circ}\text{C}$	[8] -0.01	-	+0.01	%/K
Δα	angular inaccuracy		<u>[9]</u> 0	0.05	0.1	deg

[1] Applicable for bridge 1 and bridge 2.

$$[2] \quad TC_{Vpeak} = 100 \times \frac{V_{peak}(at\ 150\ ^{\circ}C) - V_{peak}(at\ -40\ ^{\circ}C)}{V_{peak}(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[3] Bridge resistance between pin 4 to pin 8, pin 3 to pin 7, pin 1 to pin 5 and pin 2 to pin 6.

[4] 
$$TC_{Rbridge} = 100 \times \frac{R_{bridge}(at\ 150\ ^{\circ}C) - R_{bridge}(at\ -40\ ^{\circ}C)}{R_{bridge}(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[5] 
$$TC_{Voffset} = \frac{V_{offset}(at\ 150\ ^{\circ}C) - V_{offset}(at\ -40\ ^{\circ}C)}{150\ ^{\circ}C - (-40\ ^{\circ}C)}$$

$$\begin{split} [6] \quad FH_1 &= 100 \times \left| \frac{V_{O1}(67.5^\circ)135^\circ {\to} 45^\circ - V_{O1}(67.5^\circ)45^\circ {\to} 135^\circ}{2 \times V_{peak1}} \right| \\ FH_2 &= 100 \times \left| \frac{V_{O2}(22.5^\circ)90^\circ {\to} 0^\circ - V_{O2}(22.5^\circ)0^\circ {\to} 90^\circ}{2 \times V_{peak2}} \right| \end{split}$$

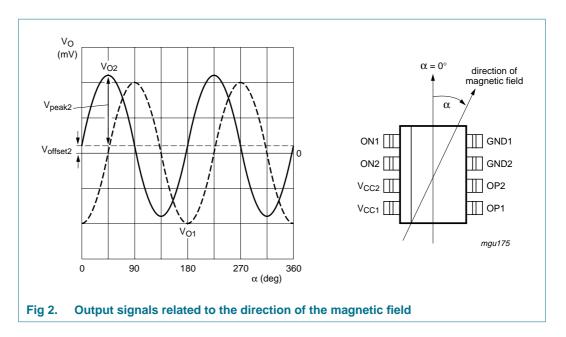
[7] 
$$k = 100 \times \frac{V_{peak1}}{V_{peak2}}$$

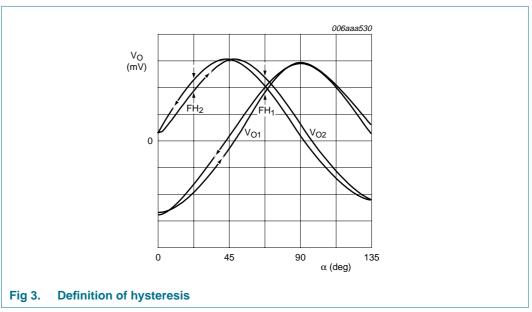
[8] 
$$TC_k = 100 \times \frac{k(at\ 150\ ^{\circ}C) - k(at\ -40\ ^{\circ}C)}{k(at\ 25\ ^{\circ}C) \times (150\ ^{\circ}C - (-40\ ^{\circ}C))}$$

[9]  $\Delta \alpha = \left| \alpha_{real} - \alpha_{meas} \right|$ ;  $V_{offset} = 0$  V; inaccuracy of angular measurement due to deviations from ideal sinusoidal characteristics, calculated from the third and fifth harmonics of the spectrum  $V_{O}$ .

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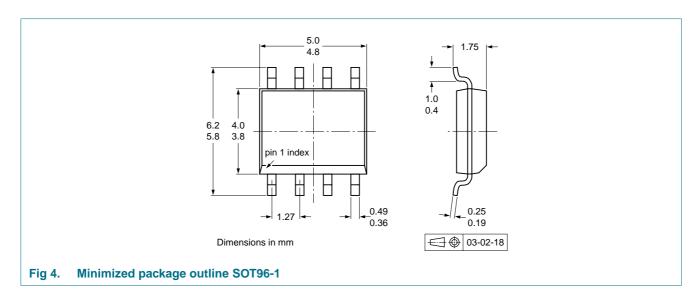
### Magnetic field sensor





**Magnetic field sensor** 

# 8. Package outline



# 9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
KMZ43T_5	20090304	Product data sheet	-	KMZ43T_4
Modifications:	• Table 6: TC <sub>V</sub>	<sub>peak</sub> and TC <sub>Rbridge</sub> values adap	oted to 25 °C referen	ce point
KMZ43T_4	20080326	Product data sheet	-	KMZ43T_3
KMZ43T_3	20030915	Product specification	-	KMZ43T_2
KMZ43T_2	20030326	Preliminary specification	-	KMZ43_1
KMZ43_1	20000824	Objective specification	-	-

## **Magnetic field sensor**

## 10. Legal information

#### 10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### Magnetic field sensor

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